

## Reflective Optical Sensor with Transistor Output



19156\_2



Top view

19156\_1

### FEATURES

- Package type: leaded
- Detector type: phototransistor
- Dimensions (L x W x H in mm): 10.2 x 5.8 x 7
- Peak operating distance: 2.5 mm
- Operating range within > 20 % relative collector current: 0.2 mm to 15 mm
- Typical output current under test:  $I_C = 1$  mA
- Daylight blocking filter
- Emitter wavelength: 950 nm
- Lead (Pb)-free soldering released
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC



**RoHS**  
COMPLIANT

### DESCRIPTION

The TCRT5000 and TCRT5000L are reflective sensors which include an infrared emitter and phototransistor in a leaded package which blocks visible light. The package includes two mounting clips. TCRT5000L is the long lead version.

### APPLICATIONS

- Position sensor for shaft encoder
- Detection of reflective material such as paper, IBM cards, magnetic tapes etc.
- Limit switch for mechanical motions in VCR
- General purpose - wherever the space is limited

### PRODUCT SUMMARY

PART NUMBER	DISTANCE FOR MAXIMUM CTR <sub>rel</sub> (1) (mm)	DISTANCE RANGE FOR RELATIVE I <sub>out</sub> > 20 % (mm)	TYPICAL OUTPUT CURRENT UNDER TEST (2) (mA)	DAYLIGHT BLOCKING FILTER INTEGRATED
TCRT5000	2.5	0.2 to 15	1	Yes
TCRT5000L	2.5	0.2 to 15	1	Yes

#### Notes

(1) CTR: current transfere ratio,  $I_{out}/I_{in}$

(2) Conditions like in table basic characteristics/sensors

### ORDERING INFORMATION

ORDERING CODE	PACKAGING	VOLUME (1)	REMARKS
TCRT5000	Tube	MOQ: 4500 pcs, 50 pcs/tube	3.5 mm lead length
TCRT5000L	Tube	MOQ: 2400 pcs, 48 pcs/tube	15 mm lead length

#### Note

(1) MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS (1)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
<b>INPUT (EMITTER)</b>				
Reverse voltage		$V_R$	5	V
Forward current		$I_F$	60	mA
Forward surge current	$t_p \leq 10 \mu s$	$I_{FSM}$	3	A
Power dissipation	$T_{amb} \leq 25^\circ C$	$P_V$	100	mW
Junction temperature		$T_j$	100	$^\circ C$

ABSOLUTE MAXIMUM RATINGS (1)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
<b>OUTPUT (DETECTOR)</b>				
Collector emitter voltage		$V_{CEO}$	70	V
Emitter collector voltage		$V_{ECO}$	5	V
Collector current		$I_C$	100	mA
Power dissipation	$T_{amb} \leq 55\text{ }^\circ\text{C}$	$P_V$	100	mW
Junction temperature		$T_j$	100	$^\circ\text{C}$
<b>SENSOR</b>				
Total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$	$P_{tot}$	200	mW
Ambient temperature range		$T_{amb}$	- 25 to + 85	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	- 25 to + 100	$^\circ\text{C}$
Soldering temperature	2 mm from case, $t \leq 10\text{ s}$	$T_{sd}$	260	$^\circ\text{C}$

**Note**

(1)  $T_{amb} = 25\text{ }^\circ\text{C}$ , unless otherwise specified

**ABSOLUTE MAXIMUM RATINGS**

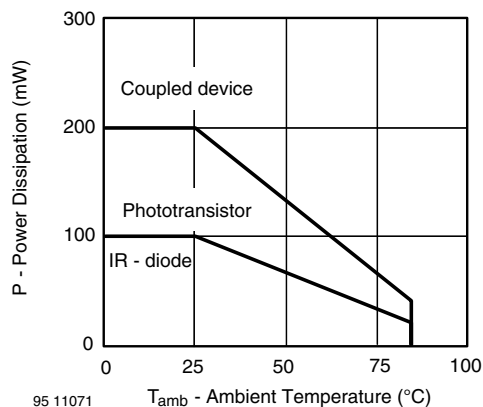


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

BASIC CHARACTERISTICS (1)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
<b>INPUT (EMITTER)</b>						
Forward voltage	$I_F = 60\text{ mA}$	$V_F$		1.25	1.5	V
Junction capacitance	$V_R = 0\text{ V}$ , $f = 1\text{ MHz}$	$C_j$		17		pF
Radiant intensity	$I_F = 60\text{ mA}$ , $t_p = 20\text{ ms}$	$I_e$			21	mW/sr
Peak wavelength	$I_F = 100\text{ mA}$	$\lambda_P$	940			nm
Virtual source diameter	Method: 63 % encircled energy	$d$		2.1		mm
<b>OUTPUT (DETECTOR)</b>						
Collector emitter voltage	$I_C = 1\text{ mA}$	$V_{CEO}$	70			V
Emitter collector voltage	$I_e = 100\text{ }\mu\text{A}$	$V_{ECO}$	7			V
Collector dark current	$V_{CE} = 20\text{ V}$ , $I_F = 0\text{ A}$ , $E = 0\text{ lx}$	$I_{CEO}$		10	200	nA
<b>SENSOR</b>						
Collector current	$V_{CE} = 5\text{ V}$ , $I_F = 10\text{ mA}$ , $D = 12\text{ mm}$	$I_C^{(2)(3)}$	0.5	1	2.1	mA
Collector emitter saturation voltage	$I_F = 10\text{ mA}$ , $I_C = 0.1\text{ mA}$ , $D = 12\text{ mm}$	$V_{CEsat}^{(2)(3)}$			0.4	V

**Note**

(1)  $T_{amb} = 25\text{ }^\circ\text{C}$ , unless otherwise specified

(2) See figure 3

(3) Test surface: mirror (Mfr. Spindler a. Hoyer, Part No. 340005)